Silicon NPN Power Transistors 2SD425 2SD426

DESCRIPTION

·With TO-3 package
·Complement to type 2SB555/556
·High power dissipation

APPLICATIONS

·Power amplifier applications
·Recommended for high-power high-fidelity audio frequency amplifier output stage

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SD425	Open emitter	140	V
		2SD426		120	
V_{CEO}	Collector-emitter voltage	2SD425	Open base	140	V
		2SD426		120	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			12	A
I_E	Emitter current			12	A
P_C	Collector power dissipation		T_C=25□	100	W
T_j	Junction temperature			150	□
T_{stg}	Storage temperature			-65~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SD425	I_C=0.1A ;I_B=0	140			V
		2SD426		120			
$V_{(BR)EBO}$	Emitter-base breakdown voltage		I_E=10mA ;I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	2SD425	I_C=7A; I_B=0.7A			3.0	V
		2SD426	I_C=6A; I_B=0.6A				
V_{BE}	Base-emitter on voltage		I_C=7A ; V_{CE}=5V			2.5	V
I_{CBO}	Collector cut-off current		V_{CB}=50V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current		V_{EB}=5V; I_C=0			0.1	mA
h_{FE}	DC current gain		I_C=2A ; V_{CE}=5V	40		140	
f_T	Transition frequency		I_C=2A ; V_{CE}=5V		5		MHz

PACKAGE OUTLINE

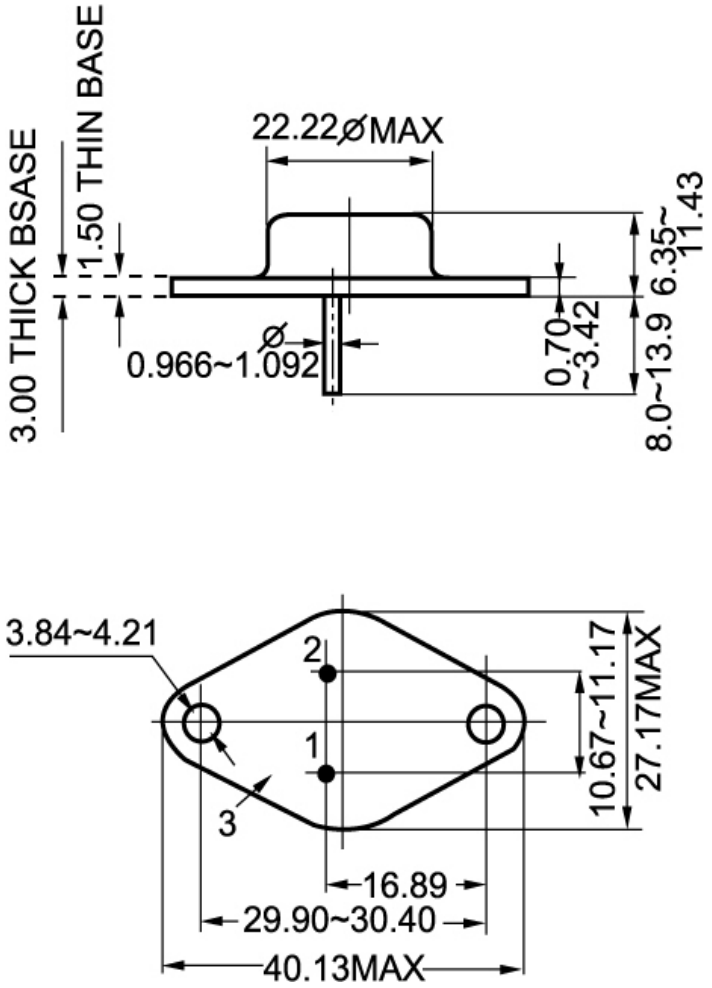


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)